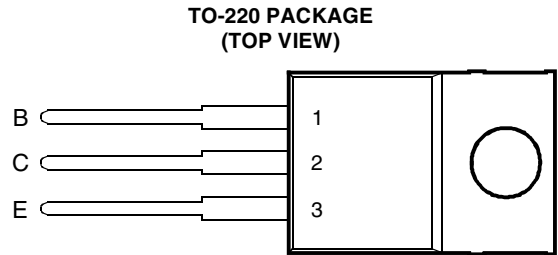


- Designed for Complementary Use with BD646, BD648, BD650 and BD652
- 62.5 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3 A



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BD645	V_{CBO}	80	V
	BD647		100	
	BD649		120	
	BD651		140	
Collector-emitter voltage ($I_B = 0$)	BD645	V_{CEO}	60	V
	BD647		80	
	BD649		100	
	BD651		120	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	8	A
Peak collector current (see Note 1)		I_{CM}	12	A
Continuous base current		I_B	0.3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	62.5	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	2	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	50	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

- NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
 4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 5$ mA, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30\text{ mA}$ $I_B = 0$ (see Note 5)	BD645 60 BD647 80 BD649 100 BD651 120			V
I_{CEO} Collector-emitter cut-off current	$V_{CE} = 30\text{ V}$ $I_B = 0$ $V_{CE} = 40\text{ V}$ $I_B = 0$ $V_{CE} = 50\text{ V}$ $I_B = 0$ $V_{CE} = 60\text{ V}$ $I_B = 0$	BD645 BD647 BD649 BD651		0.5 0.5 0.5 0.5	mA
I_{CBO} Collector cut-off current	$V_{CB} = 60\text{ V}$ $I_E = 0$ $V_{CB} = 80\text{ V}$ $I_E = 0$ $V_{CB} = 100\text{ V}$ $I_E = 0$ $V_{CB} = 120\text{ V}$ $I_E = 0$ $V_{CB} = 40\text{ V}$ $I_E = 0$ $T_C = 150^\circ\text{C}$ $V_{CB} = 50\text{ V}$ $I_E = 0$ $T_C = 150^\circ\text{C}$ $V_{CB} = 60\text{ V}$ $I_E = 0$ $T_C = 150^\circ\text{C}$ $V_{CB} = 70\text{ V}$ $I_E = 0$ $T_C = 150^\circ\text{C}$	BD645 BD647 BD649 BD651 BD645 BD647 BD649 BD651		0.2 0.2 0.2 0.2 2.0 2.0 2.0 2.0	mA
I_{EBO} Emitter cut-off current	$V_{EB} = 5\text{ V}$ $I_C = 0$ (see Notes 5 and 6)			5	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 3\text{ V}$ $I_C = 3\text{ A}$ (see Notes 5 and 6)		750		
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 12\text{ mA}$ $I_C = 3\text{ A}$ $I_B = 50\text{ mA}$ $I_C = 5\text{ A}$ (see Notes 5 and 6)			2 2.5	V
$V_{BE(sat)}$ Base-emitter saturation voltage	$I_B = 50\text{ mA}$ $I_C = 5\text{ A}$ (see Notes 5 and 6)			3	V
$V_{BE(on)}$ Base-emitter voltage	$V_{CE} = 3\text{ V}$ $I_C = 3\text{ A}$ (see Notes 5 and 6)			2.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			2.0	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	°C/W

TYPICAL CHARACTERISTICS

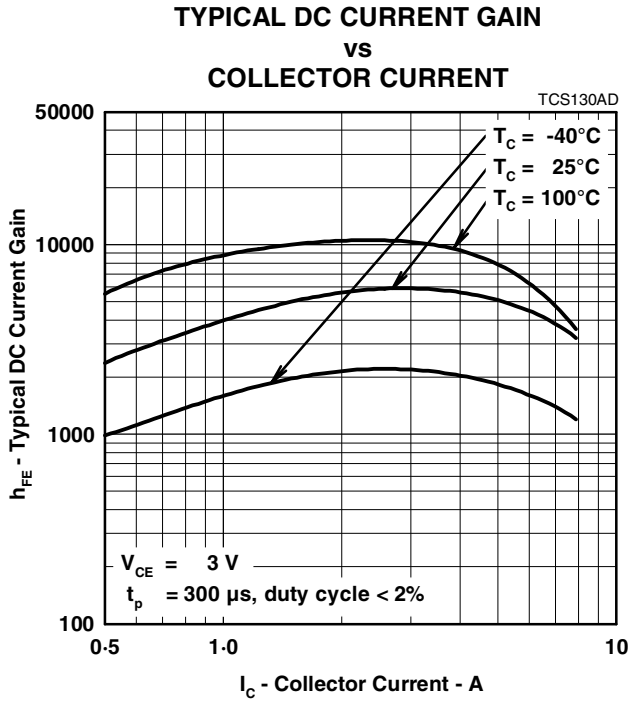


Figure 1.

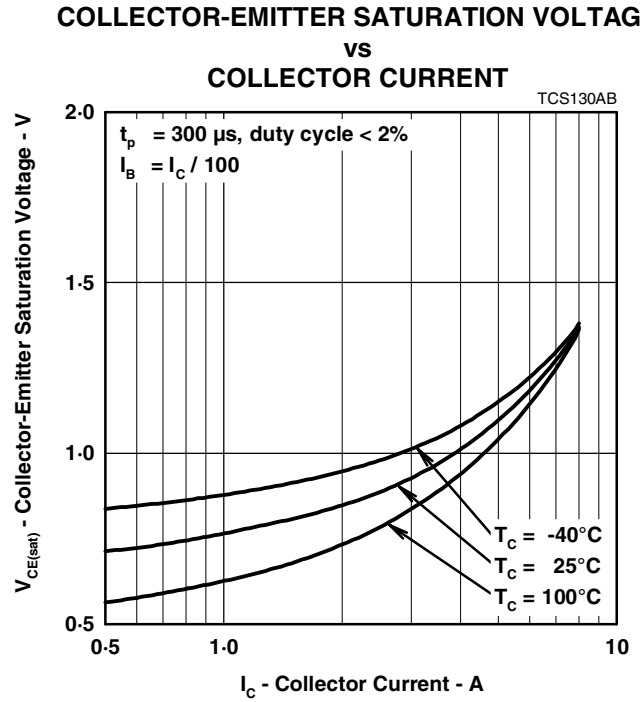


Figure 2.

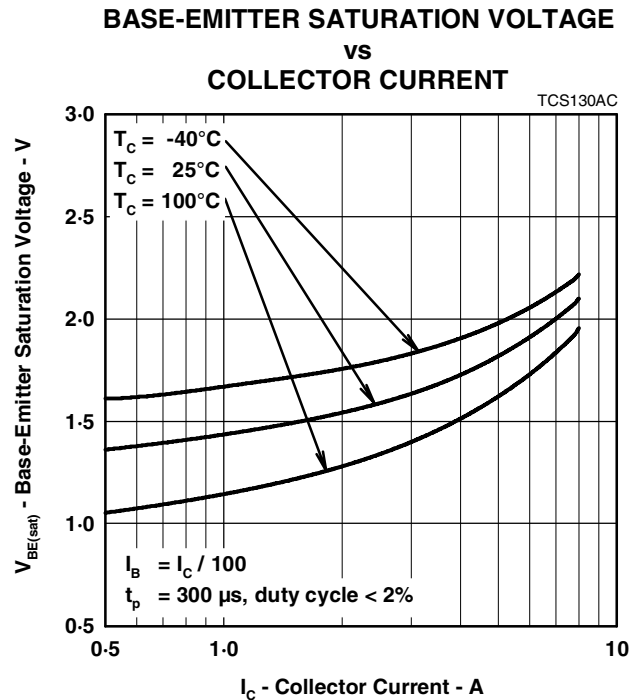


Figure 3.

PRODUCT INFORMATION

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MAXIMUM SAFE OPERATING REGIONS

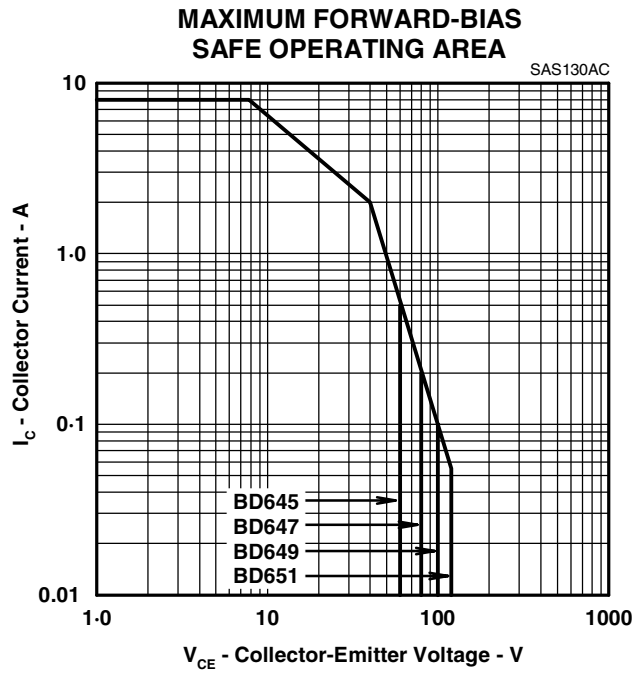


Figure 4.

THERMAL INFORMATION

**MAXIMUM POWER DISSIPATION
vs
CASE TEMPERATURE**

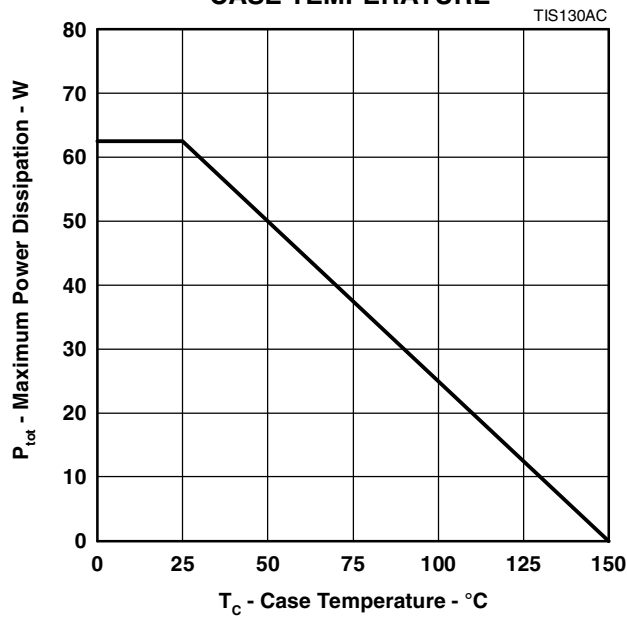


Figure 5.

PRODUCT INFORMATION

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